



TO-92MOD Plastic-Encapsulate Transistors

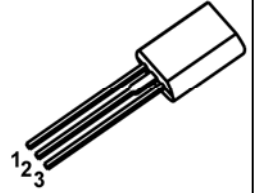
KSC2328A TRANSISTOR (NPN)

FEATURES

- Complement to KSA928A

TO – 92MOD

- 1. EMITTER
- 2. COLLECTOR
- 3. BASE



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	30	V
V _{CEO}	Collector-Emitter Voltage	30	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	2	A
P _C	Collector Power Dissipation	1	W
R _{θJA}	Thermal Resistance From Junction To Ambient	125	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	30			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =30V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =2V, I _C =500mA	100		320	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =1.5A, I _B =0.03A			2	V
Base-emitter voltage	V _{BE}	V _{CE} =2V, I _C =500mA			1	V
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		30		pF
Transition frequency	f _T	V _{CE} =2V, I _C =500mA		120		MHz

CLASSIFICATION OF h_{FE}

RANK	O	Y
RANGE	100-200	160-320